

Ordering Information

Part Number	Temp. Range	Package	Packing	RoHS Status
MDP1901TH	-55~150°C	TO-220	Tube	Halogen Free

Electrical Characteristics (Tc =25°C)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D = 250μA, V _{GS} = 0V	100	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2.0	2.8	4.0	
Drain Cut-Off Current	I _{DSS}	V _{DS} = 80V, V _{GS} = 0V	-	-	1	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V	-	-	±0.1	
Drain-Source ON Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 35A	-	17	22	mΩ
		T _J =125°C	-	28	33	
		V _{GS} = 6.0V, I _D = 20A		19	25	
Forward Transconductance	g _{fs}	V _{DS} = 5V, I _D = 35A	-	35	-	S
Dynamic Characteristics						
Total Gate Charge	Q _g	V _{DS} = 50V, I _D = 20A, V _{GS} = 10V	-	75	110	nC
Gate-Source Charge	Q _{gs}		-	20	-	
Gate-Drain Charge	Q _{gd}		-	18	-	
Input Capacitance	C _{iss}	V _{DS} = 30V, V _{GS} = 0V, f = 1.0MHz	-	3045	-	pF
Reverse Transfer Capacitance	C _{rss}		-	160	-	
Output Capacitance	C _{oss}		-	234	-	
Gate Resistance	R _g	V _{GS} =0V,V _{DS} =0V,F=1MHz	-	0.81	-	Ω
Turn-On Delay Time	t _{d(on)}	V _{GS} = 10V, V _{DS} = 50V, R _L = 30Ω, R _G = 6Ω	-	25	40	ns
Rise Time	t _r		-	12	20	
Turn-Off Delay Time	t _{d(off)}		-	70	120	
Fall Time	t _f		-	20	35	
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V _{SD}	I _S = 1A, V _{GS} = 0V	-	0.7	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 20A, dI/dt = 100A/μs	-	70	100	ns
Body Diode Reverse Recovery Charge	Q _{rr}		-	240	-	nC

Note :

1. Surface mounted RF4 board with 2oz. Copper.
2. Starting $T_J=25^\circ C$, $L=1mH$, $I_{AS}=20A$, $V_{DD}=50V$, $V_{GS}=10V$

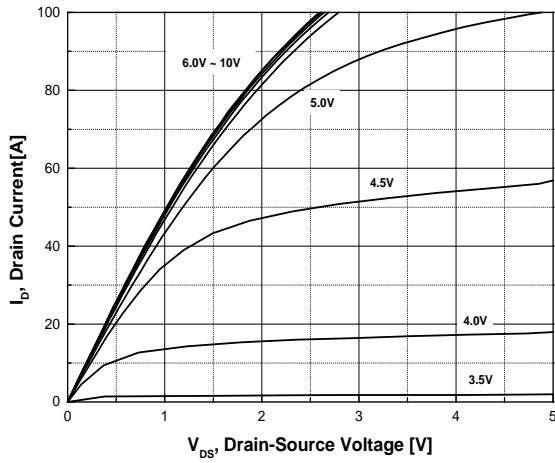


Fig.1 On-Region Characteristics

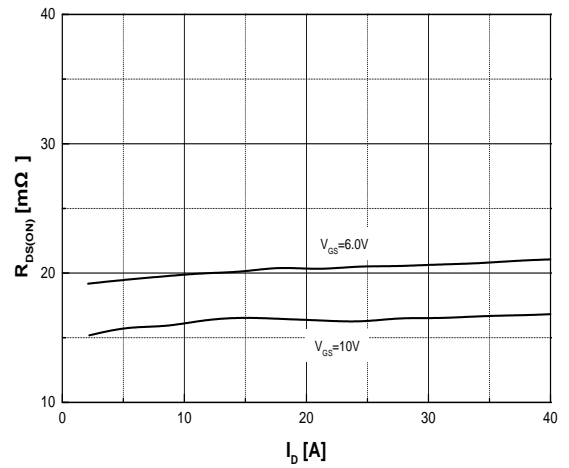


Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

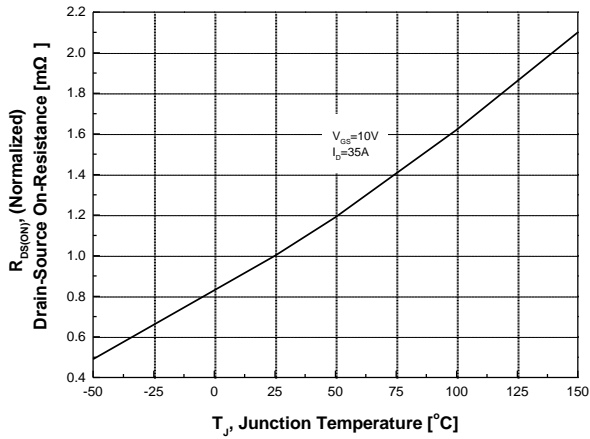


Fig.3 On-Resistance Variation with Temperature

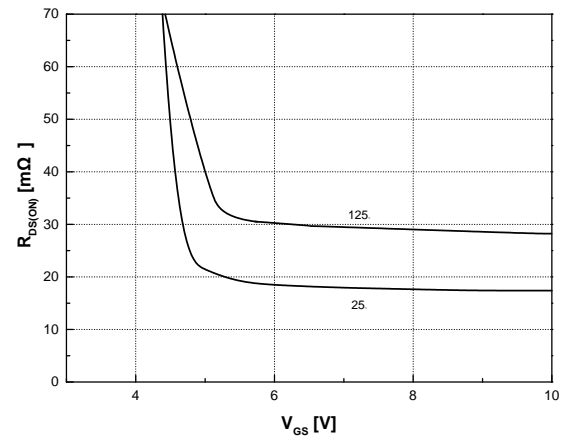


Fig.4 On-Resistance Variation with Gate to Source Voltage

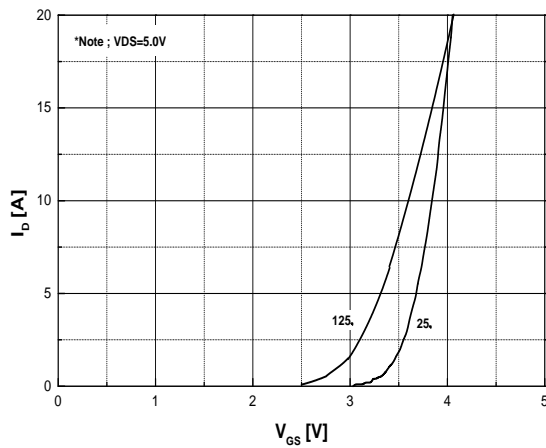


Fig.5 Transfer Characteristics

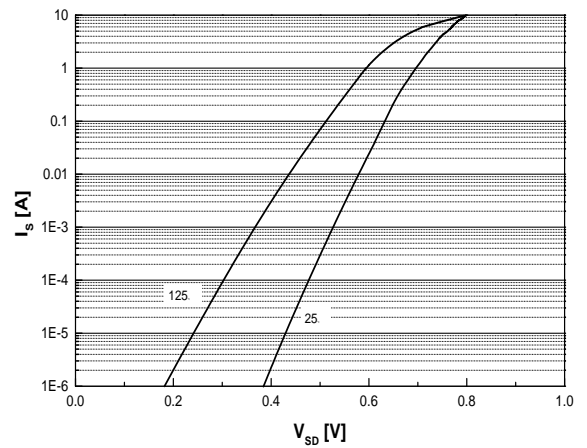


Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature

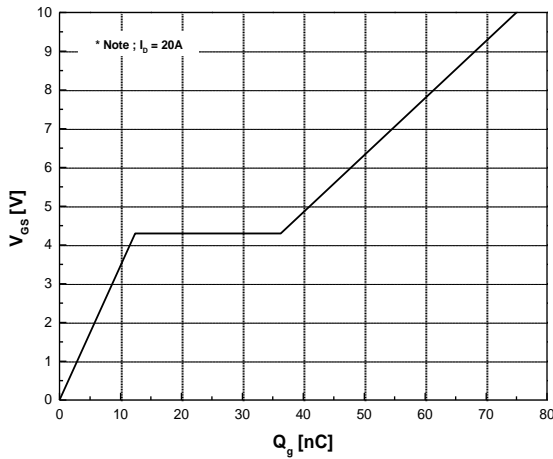


Fig.7 Gate Charge Characteristics

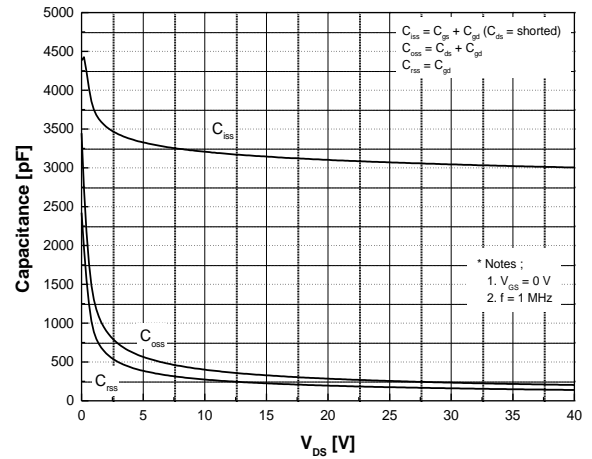


Fig.8 Capacitance Characteristics

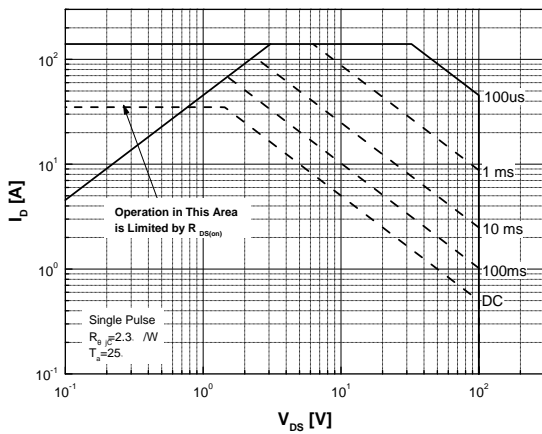


Fig.9 Maximum Safe Operating Area

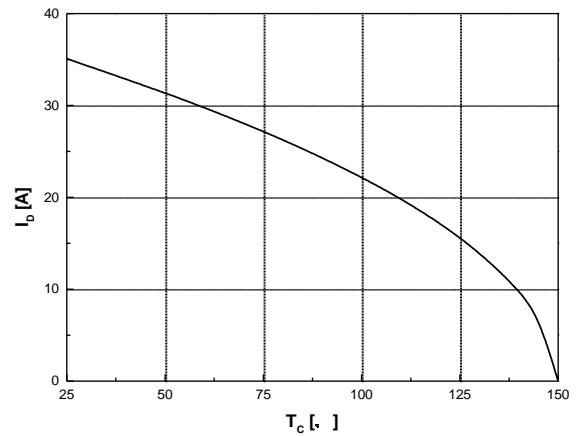


Fig.10 Maximum Drain Current vs. Case Temperature

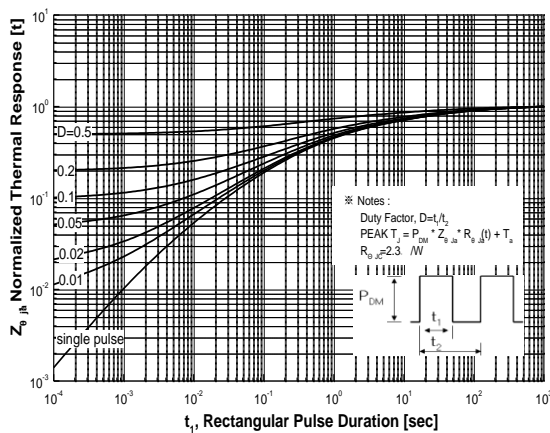
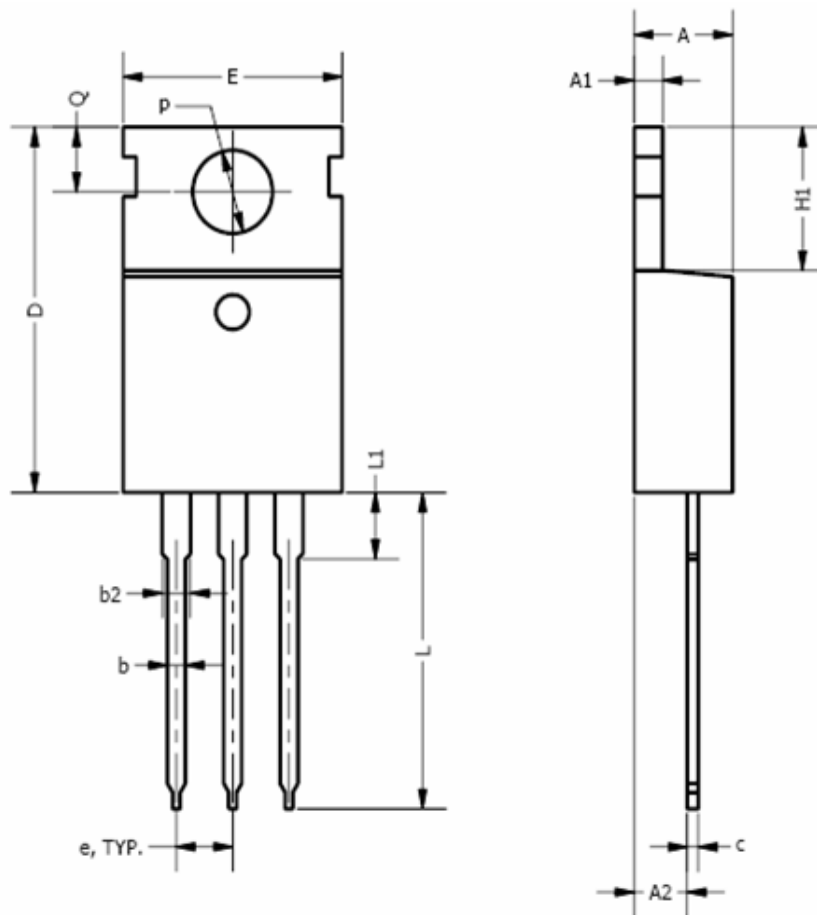


Fig.11 Transient Thermal Response Curve

Physical Dimensions

3 Leads, TO-220


Dimensions are in millimeters unless otherwise specified



Symbol	Min	Nom	Max
A	3.56		4.83
A1	0.50		1.40
A2	2.03		2.92
b	0.38	0.69	1.02
b2	1.14	1.45	1.78
c	0.36		0.61
D	14.22		16.51
e	2.54 TYP		
E	9.65		10.67
H1	5.84		6.86
L	12.70		14.73
L1			6.35
ϕP	3.53		4.09
Q	2.54		3.43

DISCLAIMER:

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